



Patent  
Attorney's Docket No. 026350-028

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )

Toshiro HIRAMOTO et al )

Application No.: 09/389,321 )

Filed: September 3, 1999 )

For: MOS TRANSISTOR WITH A )  
CONTROLLED THRESHOLD )  
VOLTAGE )

Group Art Unit: 2836

Examiner: T. Dickey

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AMENDMENT UNDER 37 C.F.R. §1.111

Assistant Commissioner for Patents  
Washington, D.C. 20231

Date: August 7, 2001

Sir:

This Amendment responds to the Office Action dated February 9, 2001 (Paper No.

6). Concurrently filed with this Amendment is a Petition for Extension of Time for a  
Three Month Period and a copy of the priority document. Please amend the above-noted  
application as follows:

IN THE ABSTRACT:

Please replace the abstract as follows:

A MOS transistor with a controlled threshold voltage includes a SOI which includes  
a substrate composed of a semi-conducting material, a single crystal layer composed of a  
semi-conducting material and an insulating layer interposed between the substrate and the  
single crystal layer. The single crystal layer is formed therein with a source region, a  
drain region and a surrounded region surrounded by the source region and the drain